**Thyristor Module** 

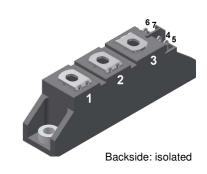
### **MCMA25P1600TA**

| $V_{\text{RRM}}$ | <i>=</i> 2x 1600 V |       |  |
|------------------|--------------------|-------|--|
| I <sub>tav</sub> | =                  | 25 A  |  |
| V <sub>T</sub>   | =                  | 1.2 V |  |

Phase leg

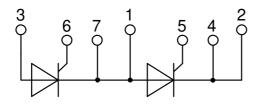
Part number

MCMA25P1600TA





20161222c



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

#### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

# LIXYS

# MCMA25P1600TA

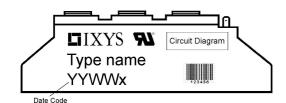
| Thyristo                 |                                    |  |   | 1    | Ratings |      |                         |
|--------------------------|------------------------------------|--|---|------|---------|------|-------------------------|
| Symbol                   | Definition                         | Conditions   |   | min. | typ.    | max. | Uni                     |
| V <sub>RSM/DSM</sub>     | max. non-repetitive reverse/forwa  | rd blocking voltage  | $T_{vJ} = 25^{\circ}C$                                  |      |         | 1700 | \<br>\                  |
| V <sub>RRM/DRM</sub>     | max. repetitive reverse/forward bl |  | $T_{VJ} = 25^{\circ}C$                                  |      |         | 1600 | ١                       |
| R/D                      | reverse current, drain current     | V <sub>R/D</sub> = 1600 V  | $T_{vJ} = 25^{\circ}C$                                  |      |         | 100  | μ/                      |
|                          |                                    | V <sub>R/D</sub> = 1600 V  | $T_{vJ} = 140^{\circ}C$                                 |      |         | 4    | m/                      |
| V <sub>T</sub>           | forward voltage drop               | $I_{T} = 25 A$   | $T_{vJ} = 25^{\circ}C$                                  |      |         | 1.22 | ١                       |
|                          |                                    | Ι <sub>τ</sub> = 50 A  |   |      |         | 1.47 | ١                       |
|                          |                                    | $I_{T} = 25 \text{ A}$   | $T_{VJ} = 125^{\circ}C$                                 |      |         | 1.20 | ١                       |
|                          |                                    | I <sub>T</sub> = 50 A  |   |      |         | 1.52 | ١                       |
| ITAV                     | average forward current            | $T_c = 85^{\circ}C$  | $T_{vJ} = 140^{\circ}C$                                 |      |         | 25   | ŀ                       |
| I <sub>T(RMS)</sub>      | RMS forward current                | 180° sine  |   |      |         | 40   | ļ                       |
| V <sub>T0</sub>          | threshold voltage                  |  | T <sub>vJ</sub> = 140°C                                 |      |         | 0.87 | ١                       |
| r <sub>T</sub>           | slope resistance } for power lo    | oss calculation only   |   |      |         | 13   | m۵                      |
| <b>R</b> <sub>thJC</sub> | thermal resistance junction to cas | e  |   |      |         | 1.2  | K/W                     |
| R <sub>thCH</sub>        | thermal resistance case to heatsi  |  |   |      | 0.20    |      | K/W                     |
| P <sub>tot</sub>         | total power dissipation            |  | $T_c = 25^{\circ}C$                                     |      |         | 90   | W                       |
| I <sub>TSM</sub>         | max. forward surge current         | t = 10 ms; (50 Hz), sine   | $T_{v,i} = 45^{\circ}C$                                 |      |         | 400  | ļ                       |
| •15M                     |                                    | t = 8,3 ms; (60 Hz), sine  | $V_{\rm R} = 0 V$                                       |      |         | 430  | ļ                       |
|                          |                                    | t = 0,0  ms; (50  Hz),  sine<br>t = 10  ms; (50  Hz),  sine  | $T_{\rm H} = 0.0$<br>$T_{\rm V,I} = 140^{\circ}{\rm C}$ |      |         | 340  |                         |
|                          |                                    | t = 8,3  ms; (60  Hz),  sine   | $V_{\rm NR} = 0 V$                                      |      |         | 365  | ,                       |
| l²t                      | value for fusing                   | t = 0.5  ms; (50  Hz),  sine   | $\frac{v_{R} = 0.7}{T_{V,I} = 45^{\circ}C}$             |      |         | 800  | A <sup>2</sup> s        |
| 1-1                      | value for fusing                   |  |   |      |         | 770  | A-s<br>A <sup>2</sup> s |
|                          |                                    | t = 8,3  ms; (60  Hz),  sine<br>t = 10  ms; (50  Hz),  sine  | $V_{\rm R} = 0 V$                                       |      |         |      | i                       |
|                          |                                    |  | $T_{VJ} = 140 ^{\circ}C$                                |      |         | 580  | A <sup>2</sup> 9        |
|                          | ium etiene en en etiene en         | t = 8,3 ms; (60 Hz), sine  | $\frac{V_{R} = 0 V}{T_{R} = 0 V}$                       |      | 10      | 555  | A <sup>2</sup> s        |
| C,                       | junction capacitance               | $V_{\rm R} = 400  \text{V}  \text{f} = 1  \text{MHz}$  | $T_{\rm VJ} = 25^{\circ}\rm C$                          |      | 16      | 10   | pl                      |
| Р <sub>GM</sub>          | max. gate power dissipation        | $t_{\rm P} = 30 \mu s$   | $T_c = 140 ^{\circ}C$                                   |      |         | 10   | W                       |
| _                        |                                    | t <sub>P</sub> = 300 μs  |   |      |         | 5    | W                       |
| P <sub>GAV</sub>         | average gate power dissipation     |  |   |      |         | 0.5  | W                       |
| (di/dt) <sub>cr</sub>    | critical rate of rise of current   | $T_{vJ} = 125 ^{\circ}C; f = 50 \text{Hz}$ re  | •   |      |         | 150  | A/μ                     |
|                          |                                    | $t_{P}$ = 200 µs; di <sub>G</sub> /dt = 0.45 A/µs; -   |   |      |         |      | <br>                    |
|                          |                                    |  | on-repet., $I_{T} = 25 A$                               |      |         |      | A/μ                     |
| (dv/dt) <sub>cr</sub>    | critical rate of rise of voltage   | $V = \frac{2}{3} V_{DRM}$  | $T_{vJ} = 125^{\circ}C$                                 |      |         | 1000 | V/µs                    |
|                          |                                    | $R_{GK} = \infty$ ; method 1 (linear volta   | ge rise)  |      |         |      |                         |
| V <sub>ат</sub>          | gate trigger voltage               | $V_{D} = 6 V$  | $T_{vJ} = 25^{\circ}C$                                  |      |         | 1.5  | ١                       |
|                          |                                    |  | $T_{vJ} = -40 ^{\circ}C$                                |      |         | 1.6  | ١                       |
| I <sub>GT</sub>          | gate trigger current               | $V_{D} = 6 V$  | $T_{v_J} = 25^{\circ}C$                                 |      |         | 55   | m/                      |
|                          |                                    |  | $T_{vJ} = -40 ^{\circ}C$                                |      |         | 80   | mÆ                      |
| V <sub>gd</sub>          | gate non-trigger voltage           | $V_{D} = \frac{2}{3} V_{DBM}$  | $T_{vJ} = 140^{\circ}C$                                 |      |         | 0.2  | ١                       |
| I <sub>GD</sub>          | gate non-trigger current           |  |   |      |         | 5    | mA                      |
|                          | latching current                   | t <sub>p</sub> = 10 μs   | $T_{vJ} = 25 ^{\circ}C$                                 |      |         | 150  | m/                      |
| -                        | -                                  | $I_{\rm g} = 0.45 \text{A};  \text{di}_{\rm g}/\text{dt} = 0.45 \text{A}/\mu\text{s}$                |   |      |         |      |                         |
| I <sub>H</sub>           | holding current                    | $V_{\rm D} = 6 V R_{\rm GK} = \infty$  | T <sub>vJ</sub> = 25°C                                  |      |         | 100  | m/                      |
| т <sub>gd</sub>          | gate controlled delay time         | $V_{\rm D} = \frac{1}{2} V_{\rm DRM}$  | $T_{vJ} = 25^{\circ}C$                                  |      |         | 2    | μ                       |
| • gd                     | gate controlled delay ante         | $I_{G} = 0.45 \text{ A}; \text{ di}_{G}/\text{dt} = 0.45 \text{ A}/\mu\text{s}$                      |   |      |         | 2    | μ                       |
| •                        | turn-off time                      | $V_{\rm R} = 100 \text{ V}; \ I_{\rm T} = 25 \text{ A}; \ V = 3200000000000000000000000000000000000$ |   |      | 150     |      |                         |
| t <sub>q</sub>           |                                    | $v_{\rm R} = 100 v, I_{\rm T} = 20 A; V = 7$   | 3 v <sub>DRM</sub> I <sub>VJ</sub> = 125 °C             |      | 150     |      | μ                       |

 $\ensuremath{\mathsf{IXYS}}$  reserves the right to change limits, conditions and dimensions.

# XYS

## **MCMA25P1600TA**

| Package                     | Package TO-240AA             |                                     |   | Ratings |      |      |      |      |
|-----------------------------|------------------------------|-------------------------------------|---|---------|------|------|------|------|
| Symbol                      | Definition                   | Conditions                          |   |         | min. | typ. | max. | Unit |
|                             | RMS current                  | per terminal                        |   |         |      |      | 60   | Α    |
| T <sub>vj</sub>             | virtual junction temperature | 9                                   |   |         | -40  |      | 140  | °C   |
| T <sub>op</sub>             | operation temperature        |                                     |   |         | -40  |      | 125  | °C   |
| T <sub>stg</sub>            | storage temperature          |                                     |   |         | -40  |      | 125  | °C   |
| Weight                      |                              |                                     |   |         |      | 81   |      | g    |
| M <sub>D</sub>              | mounting torque              |                                     |   |         | 2.5  |      | 4    | Nm   |
| M <sub>T</sub>              | terminal torque              |                                     |   |         | 2.5  |      | 4    | Nm   |
| d <sub>Spp/App</sub>        | araanaa diatanaa an aurf     | ace   striking distance through air | terminal to terminal                    | 13.0    | 9.7  |      |      | mm   |
| <b>d</b> <sub>Spb/Apb</sub> | creepage distance on sund    | ace   striking distance through an  | terminal to backside                    | 16.0    | 16.0 |      |      | mm   |
| V                           | isolation voltage            | t = 1 second                        | 50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA |         | 4800 |      |      | V    |
|                             |                              | t = 1 minute                        |   |         | 4000 |      |      | V    |



### Part description

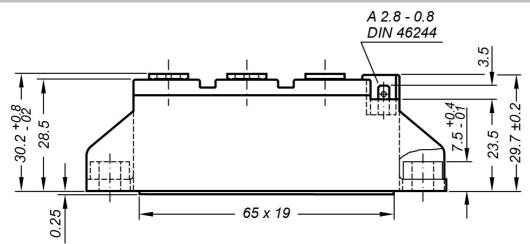
- M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 25 = Current Rating [A] P = Phase leg 1600 = Reverse Voltage [V] TA = TO-240AA-1B

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCMA25P1600TA   | MCMA25P1600TA      | Box           | 36       | 514474   |

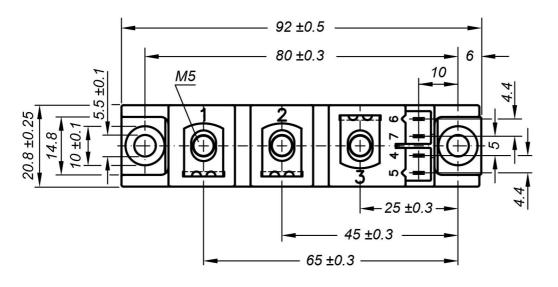
| Equiv                        | alent Circuits for | Simulation | * on die level | T <sub>vJ</sub> = 140 °C |
|------------------------------|--------------------|------------|----------------|--------------------------|
|                              | )- <u>R</u>        | Thyristor  |                |                          |
| V <sub>0 max</sub>           | threshold voltage  | 0.87       |                | V                        |
| $\mathbf{R}_{0 \text{ max}}$ | slope resistance * | 11.8       |                | mΩ                       |

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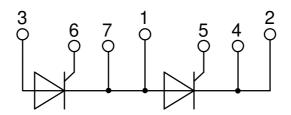
### Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



## **MCMA25P1600TA**

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### Thyristor

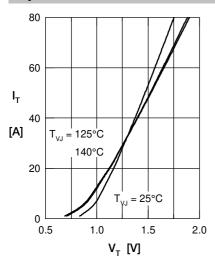


Fig. 1 Forward characteristics

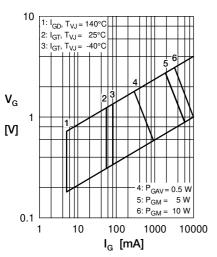


Fig. 4 Gate voltage & gate current

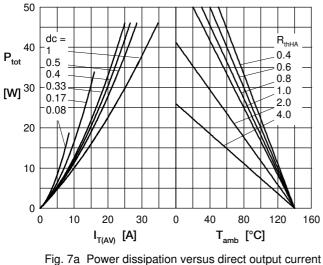
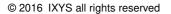
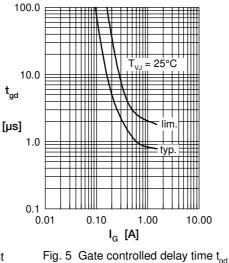


Fig. 7b and ambient temperature

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400

300

200

100

 $T_{VJ} = 140^{\circ}C$ 

0.1

t [s]

 $\mathbf{I}_{\text{TSM}}$ : crest value, t: duration

Fig. 2 Surge overload current

0.01

ITSM

[A]

50 Hz, 80% V

